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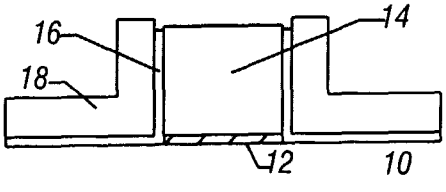
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(54) Title: FORMING POLYSILICON STRUCTURES




(57) Abstract: A doped polysilicon structure may be formed without the need to etch doped polysilicon. The patterned polysilicon (14) may be covered, an opening may be formed in the polysilicon covering (16, 18), and then the polysilicon may be doped through the opening. As a result, awkward etching of doped polysilicon may be avoided in some cases.